CPH3355

Power MOSFET -30V, 156mΩ, -2.5A, Single P-Channel



www.onsemi.com

Features

- On-resistance R_{DS}(on)1=120mΩ (typ)
- 4V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Value | Unit |
|--|------------------|-------------|------|
| Drain to Source Voltage | V _{DSS} | -30 | ٧ |
| Gate to Source Voltage | VGSS | ±20 | ٧ |
| Drain Current (DC) | ID | -2.5 | Α |
| Drain Current (Pulse) PW≤10µs, duty cycle≤1% | IDP | -10 | Α |
| Power Dissipation When mounted on ceramic substrate (900mm²x0.8mm) | PD | 1.0 | W |
| Junction Temperature | Tj | 150 | °C |
| Storage Temperature | Tstg | -55 to +150 | °C |

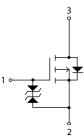
This product is designed to "ESD immunity $< 200V^*$ ", so please take care when handling.

Thermal Resistance Ratings

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|------|
| Junction to Ambient When mounted on ceramic substrate (900mm²×0.8mm) | $R_{\theta JA}$ | 125 | °C/W |

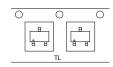
P-Channel

Electrical Connection



Packing Type:TL







Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*} Machine Model

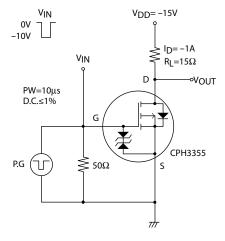
CPH3355

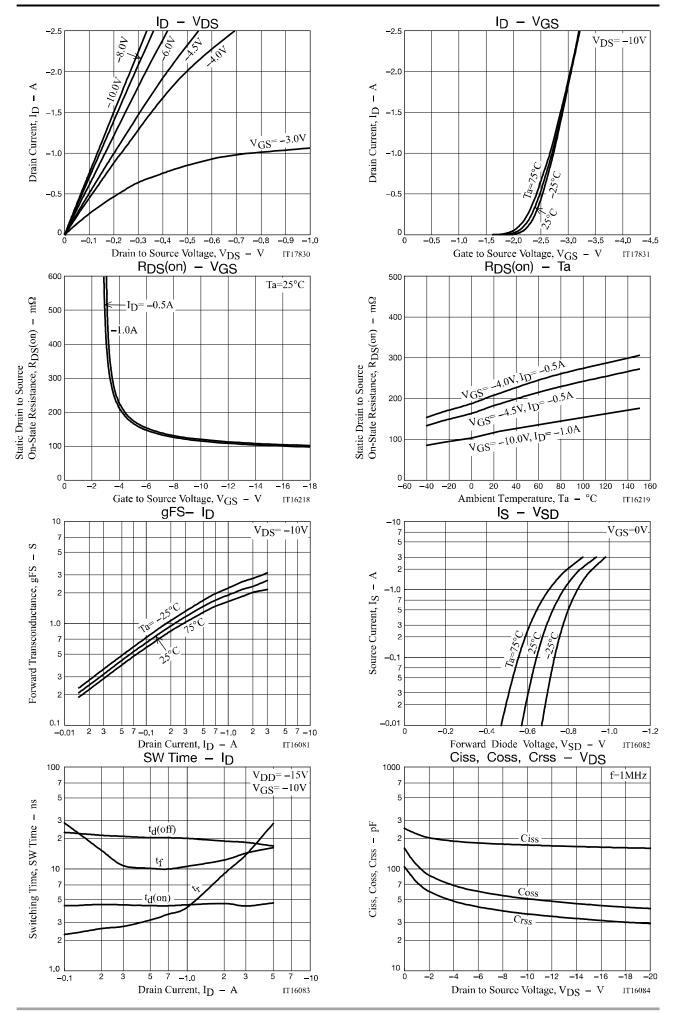
Electrical Characteristics at $Ta = 25^{\circ}C$

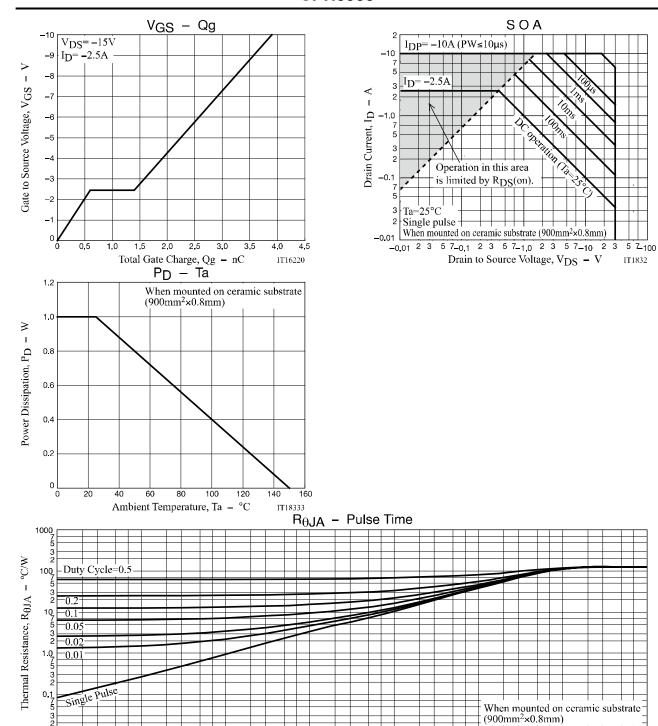
| Parameter | Symbol | Conditions | Value | | | Unit |
|--|-----------------------|---|-------|-------|------|-------|
| Parameter | Symbol | | min | typ | max | Offic |
| Drain to Source Breakdown Voltage | V(BR)DSS | I _D =-1mA, V _{GS} =0V | -30 | | | ٧ |
| Zero-Gate Voltage Drain Current | I _{DSS} | V _{DS} =-30V, V _{GS} =0V | | | -1 | μΑ |
| Gate to Source Leakage Current | IGSS | V _{GS} =±16V, V _{DS} =0V | | | ±10 | μΑ |
| Gate Threshold Voltage | V _{GS} (th) | V _{DS} =-10V, I _D =-1mA | -1.2 | | -2.6 | ٧ |
| Forward Transconductance | 9FS | V _{DS} =-10V, I _D =-1A | | 1.9 | | S |
| Static Drain to Source On-State Resistance | R _{DS} (on)1 | I _D =-1A, V _G S=-10V | | 120 | 156 | mΩ |
| | R _{DS} (on)2 | I _D =-0.5A, V _G S=-4.5V | | 187 | 262 | mΩ |
| | R _{DS} (on)3 | I _D =-0.5A, V _{GS} =-4V | | 213 | 299 | mΩ |
| Input Capacitance | Ciss | V _{DS} =-10V, f=1MHz | | 172 | | pF |
| Output Capacitance | Coss | | | 51 | | pF |
| Reverse Transfer Capacitance | Crss | | | 36 | | pF |
| Turn-ON Delay Time | t _d (on) | See specified Test Circuit | | 4.5 | | ns |
| Rise Time | t _r | | | 4.2 | | ns |
| Turn-OFF Delay Time | t _d (off) | | | 20 | | ns |
| Fall Time | tf | | | 10.6 | | ns |
| Total Gate Charge | Qg | V _{DS} =-15V, V _{GS} =-10V, I _D =-2.5A | | 3.9 | | nC |
| Gate to Source Charge | Qgs | | | 0.6 | | nC |
| Gate to Drain "Miller" Charge | Qgd |] | | 0.8 | | nC |
| Forward Diode Voltage | V _{SD} | I _S =-2.5A, V _{GS} =0V | | -0.86 | -1.5 | ٧ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







5 7 0.01

Pulse Time, PT - s

2 3

5 7 0.1

2 3

5 7 1 0

IT17698

5 70.00001 2 3 5 70.0001 2 3 5 7 0.001 2 3

Package Dimensions

CPH3355-TL-H/ CPH3355-TL-W

CPH3

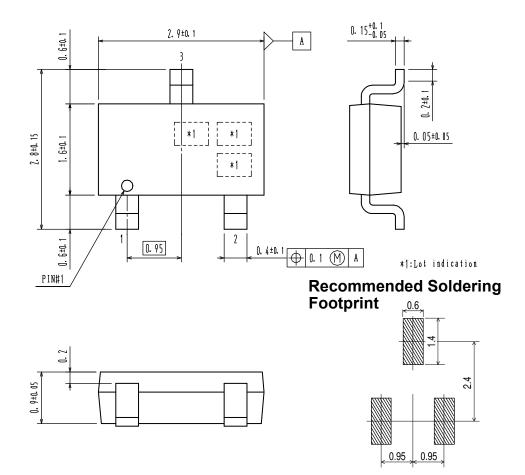
CASE 318BA ISSUE O

Unit: mm

1: Gate

2: Source

3: Drain



ORDERING INFORMATION

| Device | Package | Shipping | Note |
|--------------|----------------|-------------|---------------------|
| CPH3355-TL-H | CPH3, SC-59 | 3,000 | Pb-Free |
| CPH3355-TL-W | SOT-23, TO-236 | pcs. / reel | and Halogen Free |

Note on usage: Since the CPH3355 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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